



ELECTRONICS, INC.
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NTE26 Silicon NPN Transistor Low Noise Audio Amplifier

Features:

- $V_{CEO} = 120V$ (Min)
- Low Noise: = 1dB (Typ), 10dB (Max)

Absolute Maximum Ratings: ($T_A = +25^{\circ}C$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	120V
Collector–Emitter Voltage, V_{CEO}	120V
Emitter–Base Voltage, V_{EBO}	5V
Collector Current, I_C	100mA
Emitter Current, I_E	–100mA
Collector Dissipation, P_C	200mW
Operating Junction Temperature, T_J	+125°C
Storage Temperature Range, T_{stg}	–55° to +125°C

Electrical Characteristics: ($T_A = +25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 120V, I_E = 0$	–	–	0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	–	–	0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 6V, I_C = 2mA$	350	–	700	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$	–	–	0.3	V
Current Gain–Bandwidth Product	f_T	$V_{CE} = 6V, I_C = 1mA$	–	100	–	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	–	3.0	–	pF
Noise	NF	$V_{CE} = 6V, I_C = 0.1mA, f = 1kHz,$ $r_g = 10k\Omega$	–	1.0	10	dB

